

Taiwan Semiconductor

Glass Passivated Bridge Rectifiers

FEATURES

- Glass passivated junction
- Ideal for printed circuit board
- High case dielectric strength
- Typical IR less than 0.1µA
- High surge current capability
- UL Recognized File # E-326243
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC





KBU



MECHANICAL DATA

Case: KBU

Molding compound, UL flammability classification rating 94V-0 **Terminal:** Matte tin plated leads, solderable per JESD22-B102 Meet JESD 201 class 1A whisker test **Mounting torque:** 0.56 N·m max. **Weight:** 7.2 g (approximately)

		KBU KBU KBU			KBU	KBU	KBU	KBU	
PARAMETER	SYMBOL	601G	602G	603G	604G	605G	606G	607G	Unit
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current	I _{F(AV)}	6			Α				
Peak forward surge current, 8.3 ms single half sine-wave superimposed on rated load	I _{FSM}	175				A			
Rating for fusing (t<8.3ms)	l ² t	127				A ² s			
Maximum instantaneous forward voltage (Note 1) $I_{\rm F}{=}$ 3 A $I_{\rm F}{=}$ 6 A	V _F	1.0 1.1			V				
Maximum DC reverse current $T_J=25 \degree$ at rated DC blocking voltage $T_J=125\degree$	I _R	5 500			μA				
Typical junction capacitance per leg	Cj	400			pF				
Typical thermal resistance	R _{θJC} R _{θJA}	3.1 8.6			^o C/W				
Operating junction temperature range	TJ	- 55 to +150			°C				
Storage temperature range	T _{STG}	- 55 to +150			°C				

Note 1: Pulse Test with PW=300µs, 1% Duty Cycle

Note 2: Measured at 1MHz and applied Reverse Voltage of 4.0V D.C.



KBU601G thru KBU607G

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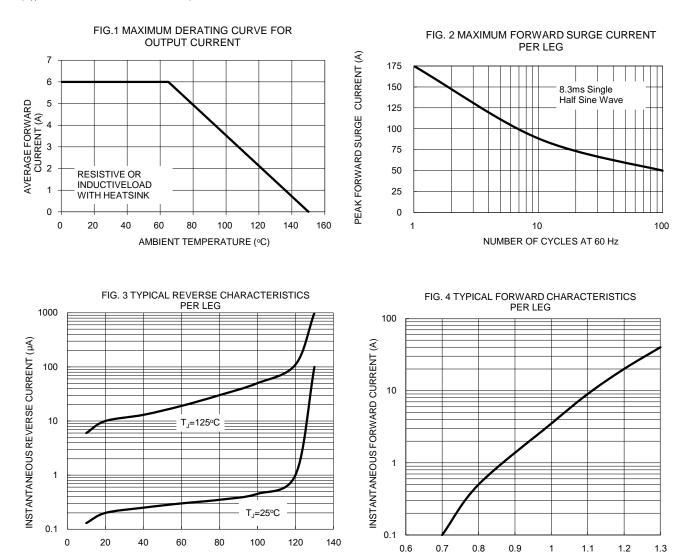
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING			
KBU601G T0	KBU	500 / Trays			
KBU602G T0	KBU	500 / Trays			
KBU603G T0	KBU	500 / Trays			
KBU604G T0	KBU	500 / Trays			
KBU605G T0	KBU	500 / Trays			
KBU606G T0	KBU	500 / Trays			
KBU607G T0	KBU	500 / Trays			

RATINGS AND CHARACTERISTICS CURVES

PERCENT OF RATED PEAK REVERSE VOLTAGE (V)

(T_A=25°C unless otherwise noted)

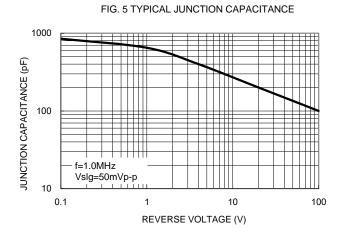


INSTANTANEOUS FORWARD VOLTAGE (V)



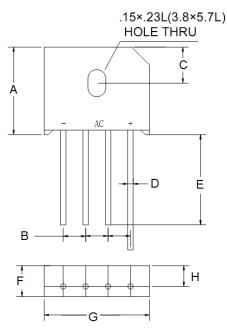
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PACKAGE OUTLINE DIMENSIONS





P/N

F

DIM.	Unit	(mm)	Unit (inch)		
DINI.	Min	Max	Min	Max	
А	18.8	19.8	0.740	0.780	
В	4.6	5.6	0.181	0.220	
С	8.2 (TYP.)		0.322 (TYP.)		
D	1.2	1.3	0.047	0.051	
Е	20.0	-	0.787	-	
F	6.8	7.1	0.268	0.280	
G	22.7	23.7	0.894	0.933	
Н	4.6	5.0	0.181	0.197	

MARKING DIAGRAM



- = Specific Device Code
- YWW = Date Code
 - = Factory Code



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